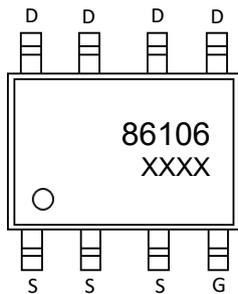


Features

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

Application

- Consumer electronic power supply
- Motor control
- Synchronous-rectification
- Isolated DC/DC convertor



Marking and pin assignment

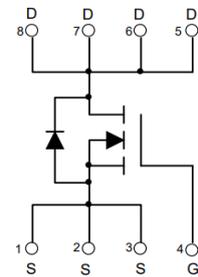
 86106 : Device code
 XXXX : Code

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
100V	85mΩ@10V	3.4A
	90mΩ@6V	



SOP-8 top view



Schematic diagram



Pb-Free



Halogen-Free

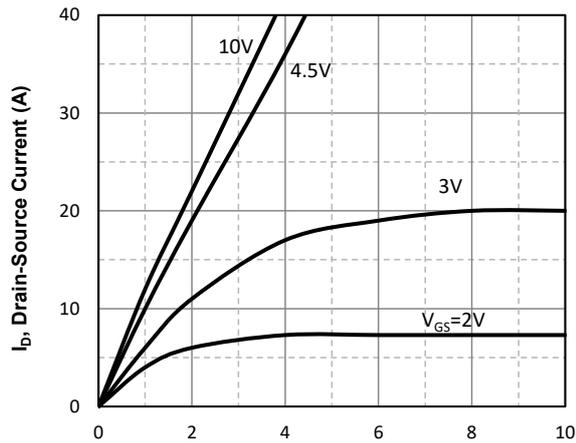
Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$ 3.4	A
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$ 15	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$ 3.4	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$ 4.8	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	50	°C/W

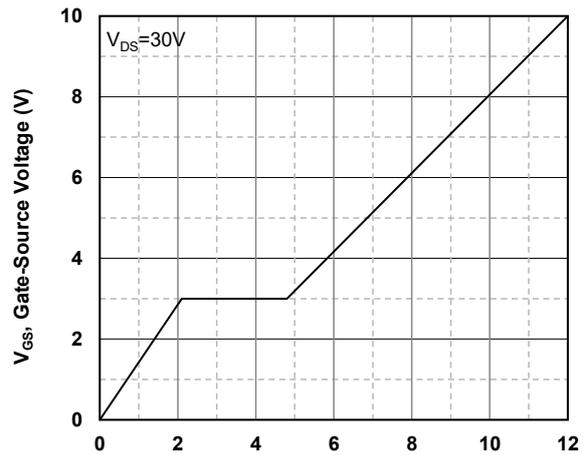
Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSQ86106	SOP-8	86106	3,000	6,000	42,000	13"reel

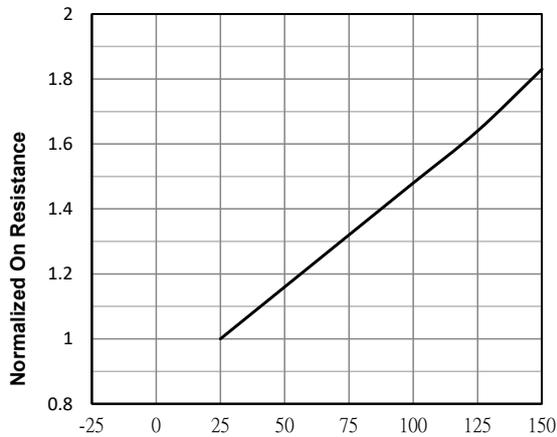
Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =3.7A	--	85	105	mΩ
		V _{GS} =6V, I _D =2.7A	--	90	171	mΩ
		V _{GS} =4.5V, I _D =1.0A	--	95	220	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	--	760	--	pF
C _{OSS}	Output Capacitance		--	38	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	33	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =30V, I _D =5A, V _{GS} =10V	--	12	--	nC
Q _{gs}	Gate Source Charge		--	2.2	--	nC
Q _{gd}	Gate Drain Charge		--	2.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =10A, V _{GS} =10V, R _G =1.8Ω	--	7	--	nS
t _r	Turn-on Rise Time		--	5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	15	--	nS
t _f	Turn-Off Fall Time		--	6	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =1.8A,	--	--	1.2	V

Typical Operating Characteristics


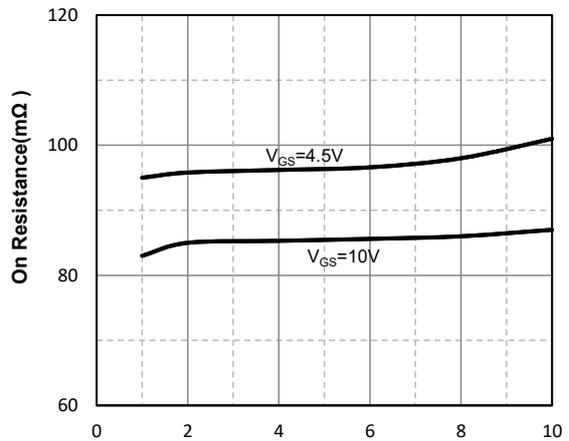
V_{DS}, Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



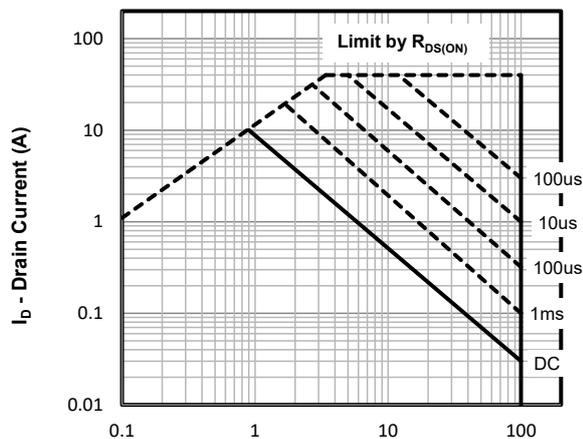
Qg -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs. Gate-Source Voltage



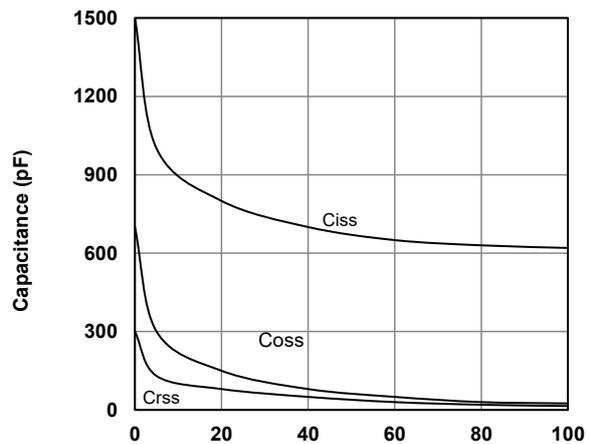
T_j - Junction Temperature (°C)
Fig3. Normalized On-Resistance Vs. Temperature



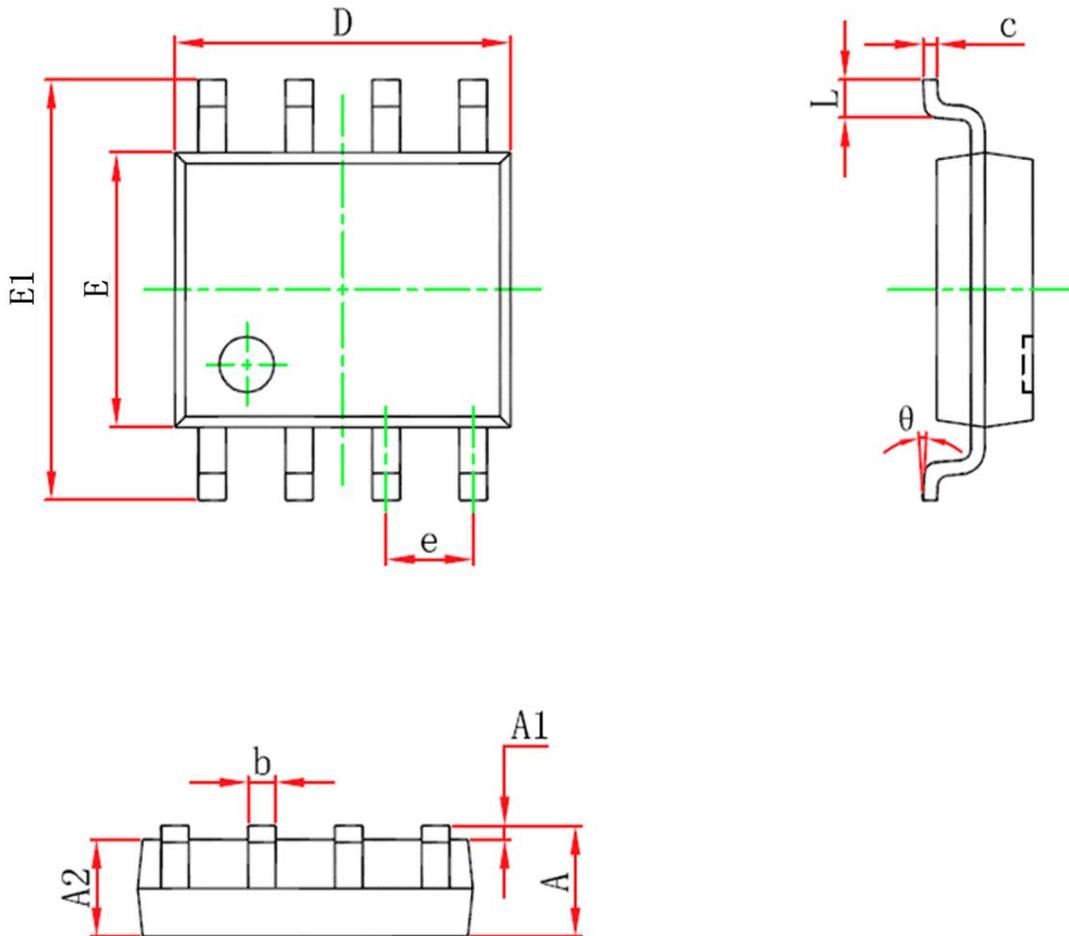
I_D, Drain-Source Current (A)
Fig4. On-Resistance Vs. Drain-Source Current



V_{DS}, Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



V_{DS}, Drain-Source Voltage (V)
Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOP-8 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°